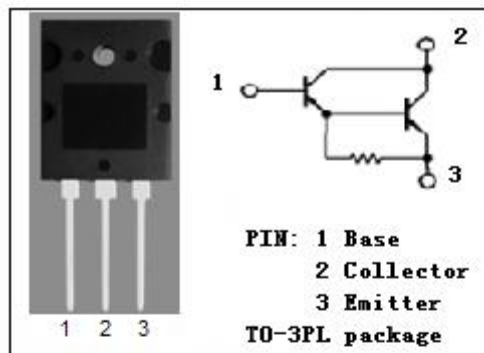


isc Silicon PNP Darlington Power Transistor**2SB1503****DESCRIPTION**

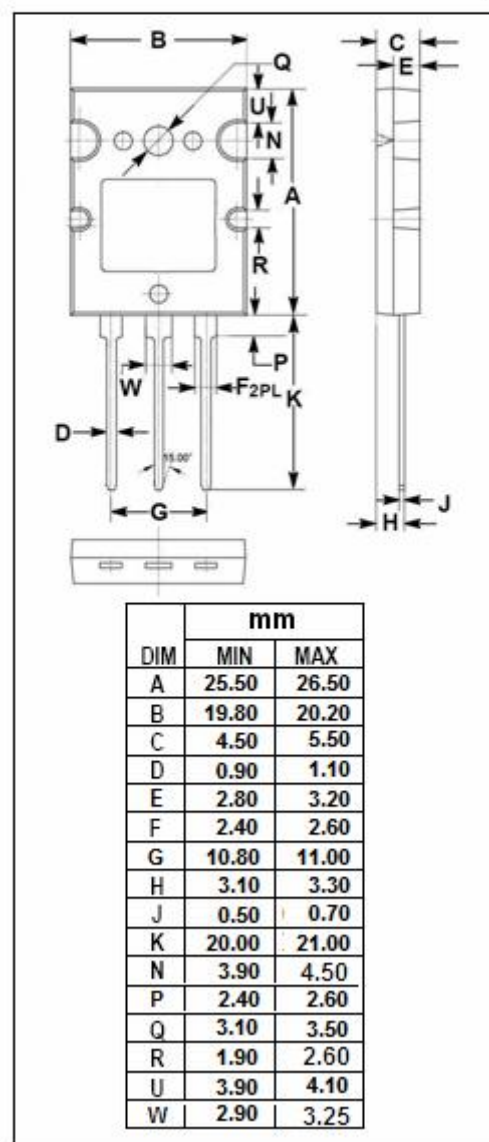
- High DC Current Gain-
: $h_{FE} = 5000(\text{Min}) @ I_C = -7\text{A}$
- Low-Collector Saturation Voltage-
: $V_{CE(\text{sat})} = -2.5\text{V}(\text{Max.}) @ I_C = -7\text{A}$
- Complement to Type 2SD2276
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for power amplifier applications
- Optimum for 110W HiFi output applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-140	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-7	A
I_{CM}	Collector Current-Peak	-12	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	120	W
	Collector Power Dissipation @ $T_a = 25^\circ\text{C}$	3.5	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon PNP Darlington Power Transistor**2SB1503****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -30\text{mA}$; $I_B = 0$	-140			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -7\text{A}$; $I_B = -7\text{mA}$			-2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -7\text{A}$; $I_B = -7\text{mA}$			-3.0	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -160\text{V}$; $I_E = 0$			-100	μA
I_{CEO}	Collector Cutoff Current	$V_{CE} = -140\text{V}$; $I_B = 0$			-100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}$; $I_C = 0$			-100	μA
h_{FE-1}	DC Current Gain	$I_C = -1\text{A}$; $V_{CE} = -5\text{V}$	2000			
h_{FE-2}	DC Current Gain	$I_C = -7\text{A}$; $V_{CE} = -5\text{V}$	5000		30000	
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}$; $V_{CE} = -10\text{V}$		20		MHz

Switching Times

t_{on}	Turn-on Time	$I_C = -7\text{A}$; $I_{B1} = -I_{B2} = -7\text{mA}$, $V_{CC} = -50\text{V}$		1.0		μs
t_{stg}	Storage Time			1.5		μs
t_f	Fall Time			1.2		μs

◆ **h_{FE-2} Classifications**

Q	S	P
5000-15000	7000-21000	8000-30000

isc Silicon PNP Darlington Power Transistor**2SB1503****Notice:**

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